

## **THYRISTOR(Surface Mount Device/Non-isolated)**

# **SMG2D60D**

## (Sensitive Gate)

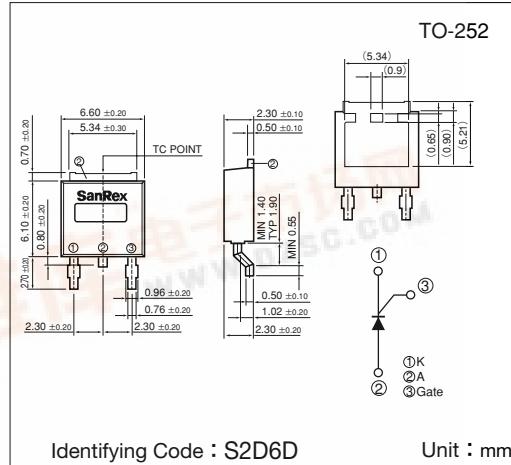
**SanRex** Thyristor **SMG2D60D** is designed for full wave AC control applications. It can be used as an ON/OFF function or for phase control operation.

## Typical Applications

- Home Appliances : Electric Blankets, Starter for FL, other control applications
  - Industrial Use : SMPS, Solenoid for Breakers, Motor Controls, Heater Controls, other control applications

## Features

- $I_{T(AV)}=2A$
  - High Surge Current
  - Low Voltage Drop
  - Lead-Free Package



Identifying Code : S2D6D

Unit : mm

## ■ Maximum Ratings

(T<sub>j</sub>=25°C unless otherwise specified)

Symbol	Item	Reference	Ratings	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage		600	V
$V_{RSM}$	Non-Repetitive Peak Reverse Voltage		720	V
$V_{DRM}$	Repetitive Peak Off-State Voltage		600	V
$I_{T(AV)}$	Average On-State Current	Single phase, half wave, 180°, conduction, $T_c=108^\circ C$	2	A
$I_{T(RMS)}$	R.M.S. On-State Current	Single phase, half wave, 180°, conduction, $T_c=108^\circ C$	3.1	A
$I_{TSM}$	Surge On-State Current	50Hz/60Hz, ½ cycle Peak value, non-repetitive	30/33	A
$I^2t$	$I^2t$		4.5	$A^2S$
$P_{GM}$	Peak Gate Power Dissipation		0.5	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.1	W
$I_{FGM}$	Peak Gate Current		0.3	A
$V_{FGM}$	Peak Gate Voltage (Forward)		6	V
$V_{RGM}$	Peak Gate Voltage (Reverse)		6	V
$T_j$	Operating Junction Temperature		-40~+125	$^\circ C$
$T_{stg}$	Storage Temperature		-40~+150	$^\circ C$
	Mass		0.32	g

### ■ Electrical Characteristics

Symbol	Item	Reference	Ratings			Unit
			Min.	Typ.	Max.	
I <sub>DRM</sub>	Repetitive Peak Off-State Current	T <sub>j</sub> =125°C, V <sub>D</sub> =V <sub>DRM</sub> , R <sub>GK</sub> =220Ω			1	mA
I <sub>RRM</sub>	Repetitive Peak Reverse Current	T <sub>j</sub> =125°C, V <sub>R</sub> =V <sub>RRM</sub> , R <sub>GK</sub> =220Ω			1	mA
V <sub>TM</sub>	Peak On-State Voltage	I <sub>T</sub> =6A, Inst. measurement			1.5	V
I <sub>GT</sub>	Gate Trigger Current	V <sub>D</sub> =6V, R <sub>L</sub> =10Ω		1	200	μA
V <sub>GT</sub>	Gate Trigger Voltage				0.8	V
V <sub>GD</sub>	Non-Trigger Gate Voltage	T <sub>j</sub> =125°C, V <sub>D</sub> =½V <sub>DRM</sub> , R <sub>GK</sub> =220kΩ	0.1			V
I <sub>H</sub>	Holding Current	R <sub>GK</sub> =220Ω		3.5		mA
R <sub>th(j-c)</sub>	Thermal Resistance	Junction to case			5.8	°C/W

